

In re Appln. of KISE et al.
Application No. Unassigned

SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 14 with:

The resolution limit L determined by Fresnel diffraction is provided by:

$$L=k \times (\lambda \times D)^{1/2}$$

where k is a constant, λ is an exposure wavelength, and D is the distance between an x-ray mask and a wafer. This equation shows that, the shorter the exposure wavelength and the smaller the distance between the x-ray mask and the wafer, the higher the resolution can be obtained.

Replace the paragraph beginning at page 1, line 21 with:

On the other hand, blur caused by secondary electrons generated in a resist by x-ray irradiation has been considered to decrease as the exposure wavelength increases, as described by Takigawa in "The Innovation of ULSI Lithography", published by Science Forum Co. Ltd., 1st edition, at page 222. Thus, it has been considered that the longer the exposure wavelength, the higher the resolution can be obtained.